

2MBI200VB-120-50

IGBT Modules

IGBT MODULE (V series) 1200V / 200A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



■ Maximum Ratings and Characteristics

◆ Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items	Symbols	Conditions	Conditions		Units	
Collector-Emitter voltage	Vces			1200	V	
Gate-Emitter voltage	V _{GES}			±20	V	
Collector current	Ic	Continuous	Tc=100°C	200		
	I _{C pulse}	1ms		400		
	-lc			200		
	-I _{C pulse}	1ms		400		
Collector power dissipation	Pc	1 device		1500	W	
Junction temperature	T _j			175		
Operating junction temperature (under switching conditions	S) T _{jop}			150	°C	
Case temperature	Tc			125		
Storage temperature	T _{stg}			-40 ~ 125		
Isolation voltage between terminal and copper base (*1)	Viso	AC : 1min.		2500	VAC	
Sorous forgue Mounting (*2)	-			3.5	Nm	
Screw torque Terminals (*3)	-			3.5	Nm	

Note *1: All terminals should be connected together during the test.

Note *2: Recommendable Value : 2.5-3.5 Nm (M5 or M6) Note *3: Recommendable Value : 2.5-3.5 Nm (M5)

● Electrical characteristics (at T_j= 25°C unless otherwise specified)

lt	Symbolo	Symbols Conditions		Characteristics		ics	I I mit m
Items	Symbols			min.	typ.	max.	Units
Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1200V		-	-	2.0	mA
Gate-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	400	nA
Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 200mA		6.0	6.5	7.0	V
Collector-Emitter saturation voltage	V	V _{GE} = 15V I _C = 200A	T _j =25°C	-	1.95	2.40	V
	V _{CE (sat)} (terminal)		T _j =125°C	-	2.25	-	
	(terminar)		T _j =150°C		2.30		
	V	V _{GE} = 15V I _C = 200A	T _j =25°C	-	1.75	2.20	
	V _{CE} (sat)		T _j =125°C	-	2.05	-	
	(chip)		T _j =150°C		2.1		
Internal gate resistance	R _G (int)	-		-	3.8	-	Ω
Input capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	18.2	-	nF
Turn-on time	ton	$V_{CC} = 600V$ $I_{C} = 200A$ $V_{GE} = \pm 15V$ $R_{G} = 2.7\Omega$ $T_{J} = 150^{\circ}C$		-	600	-	nsec
	tr			-	200	-	
	t _{r (i)}			-	50	-	
Turn-off time	toff			-	800	-	
	tr			-	80	-	
Forward on voltage	VF	V _{GE} = 0V I _F = 200A	T _j =25°C	-	1.85	2.30	V
	(terminal)		T _j =125°C	-	2.00	-	
	(terminar)		T _j =150°C		1.95		
	VF	V _{GE} = 0V I _F = 200A	T _i =25°C	-	1.70	2.15	
			T _j =125°C	-	1.85	-	
	(chip)		T _j =150°C		1.80		
Reverse recovery time	trr	I _F = 200A	·	-	150	-	nsec

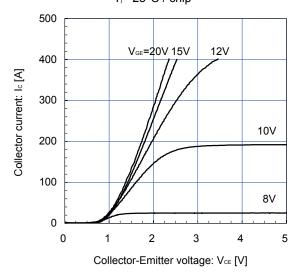
Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
		Conditions	min.	typ.	max.	Ullits
Thermal resistance (1device)	R _{th(j-c)}	IGBT	-	-	0.100	°C/W
		FWD	-	-	0.160	
Contact thermal resistance (1device) (*4)	R _{th(c-f)}	with Thermal Compound	-	0.025	-	

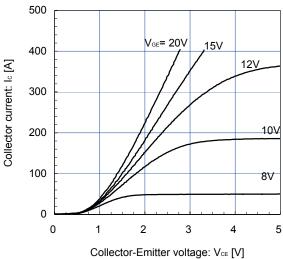
Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

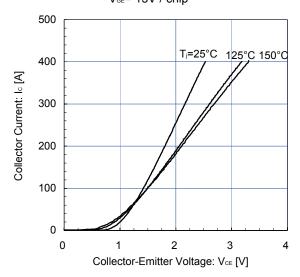
Collector current vs. Collector-Emitter voltage (typ.) T_i = 25°C / chip



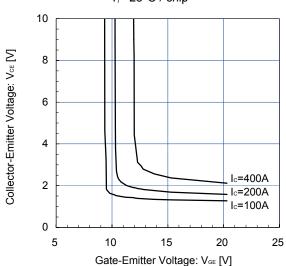
Collector current vs. Collector-Emitter voltage (typ.) T_j = 150°C / chip



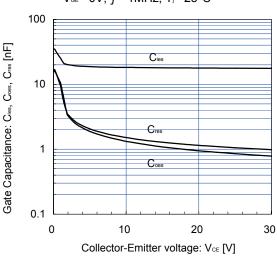
Collector current vs. Collector-Emitter voltage (typ.) V_{GE} = 15V / chip



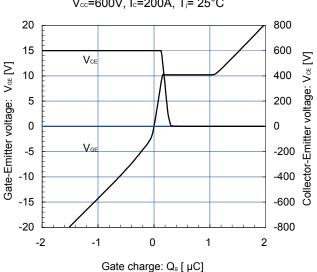
Collector-Emitter voltage vs. Gate-Emitter voltage T_j= 25°C / chip

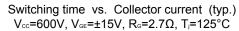


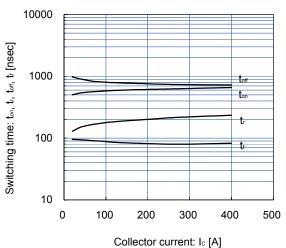
Gate Capacitance vs. Collector-Emitter Voltage V_{GE} = 0V, f= 1MHz, T_{J} = 25°C



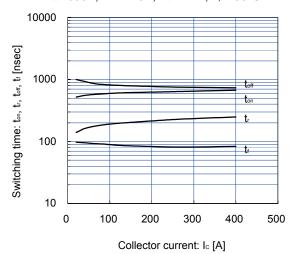
Dynamic Gate Charge (typ.) Vcc=600V, Ic=200A, T_i= 25°C



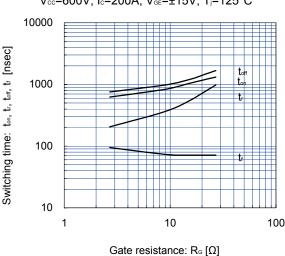




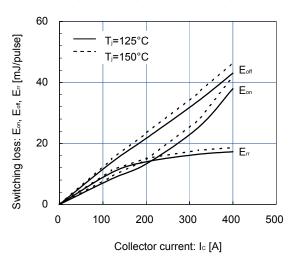
Switching time vs. Collector current (typ.) V_{cc} =600V, V_{ce} =±15V, R_c =2.7 Ω , T_j =150°C



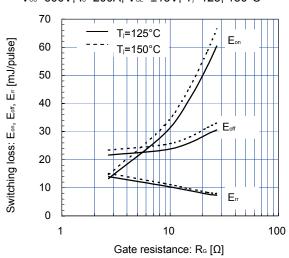
Switching time vs. Gate resistance (typ.) V_{CC} =600V, I_{C} =200A, V_{GE} =±15V, T_{J} =125°C



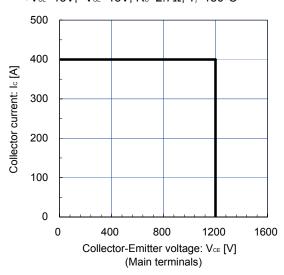
Switching loss vs. Collector current (typ.) V_{cc} =600, V_{ce} =±15V, R_{c} =2.7 Ω , T_{j} =125, 150°C



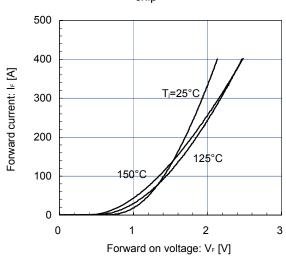
Switching loss vs. Gate resistance (typ.) V_{cc} =600V, I_c =200A, V_{cE} =±15V, T_j =125, 150°C



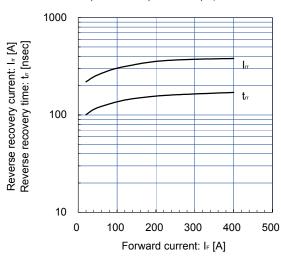
Reverse bias safe operating area (max.) $+V_{GE}=15V$, $-V_{GE}=15V$, $R_{G}=2.7\Omega$, $T_{J}=150^{\circ}C$



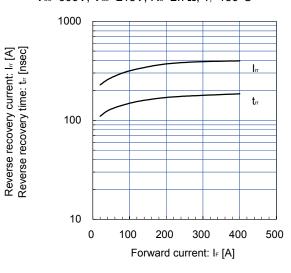
Forward Current vs. Forward Voltage (typ.) chip



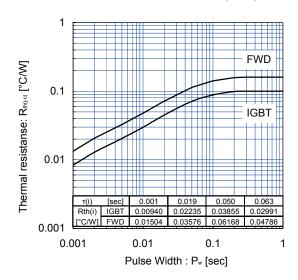
Reverse Recovery Characteristics (typ.) V_{cc} =600V, V_{ce} =±15V, R_c =2.7 Ω , T_j =125°C



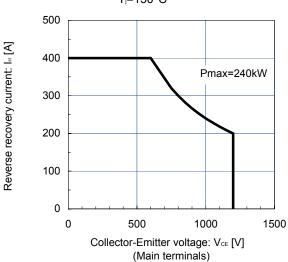
Reverse Recovery Characteristics (typ.) V_{CC} =600V, V_{GE} =±15V, R_{G} =2.7 Ω , T_{j} =150°C



Transient Thermal Resistance (max.)

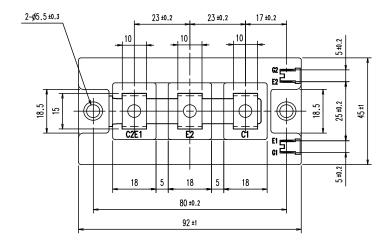


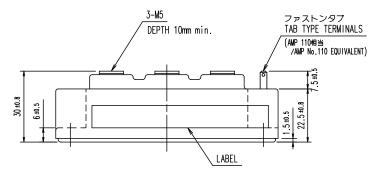
FWD safe operating area (max.) T=150°C



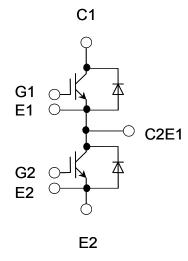
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■ Outline Drawings, mm





■ Equivalent Circuit Schematic



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